The Second Japan-China Joint Workshop on GaN-based Materials and Devices

Date: September 25 (Fri), 2009
Venue: Capital Hotel
Language: English

Program

Chair: Guohong Wang (Institute of Semiconductors, CAS)

09:30-09:35 Opening address

Jinmin Li (Director General， Institute of Semiconductors, CAS)

Takashi Egawa (Director，Research Center for Nano-Device and System, Nagoya Institute of Technology)

09:35-09:40 Honorary Professor Ceremony

09:45-10:10 Jicai Zhang (Nagoya Institute of Technology)

AlGaN deep ultraviolet LED with different template,J. Zhang and T. Egawa

10:10-10:35 Zhitao Chen (Nagoya Institute of Technology)

InAlN-based solar-blind photodiode grown by MOCVD, Z. Chen and T. Egawa

10:35-11:00 Youhua Zhu (Nagoya Institute of Technology)

InGaN bule LED grown on 3C-SiC/Si (111), Y. Zhu and T. Egawa

11:00-11:25 Y. Aoki (Nagoya Institute of Technology)

Electrical characterization for GaN with low energy electron irradiation,Y. Aoki, M. Kasuga, M. Kato, M. Ichimura

11:25-11:50 Kunyuan Xu (Sun Yat-Sen University)

Study of THz oscillations in GaN-based planar nanodevices

12:00 Lunch

Chair: Takashi Egawa（Nagoya Institute of Technology）

13:30-13:55 Junxi Wang （Institute of Semiconductors, CAS）

Deep-UV LEDs material growth and application

13.55-14.20 Ruifei Duan （Institute of Semiconductors, CAS）

Performance enhancemnt of GaN LED homoepitaxy using InGaN prewells

14.20-14.45 Hongling Xiao （Institute of Semiconductors, CAS）

Research on InGaN for photovoltaic materials and devices

14.45-15.10 Qiang Hu （Institute of Semiconductors, CAS）

HVPE grown thick GaN film on wet-etching patterned sapphire

15:10-15.30 Coffee break

Chair: Gang Wang (Sun Yat-Sen University)

15.30-15:55 Lili Sun （Institute of Semiconductors, CAS）

Effect of Indium Tin Oxide (ITO) on the Activation of Mg-doped GaN Films

15:55-16:20 Zhiqiang Liu (Institute of Semiconductors, CAS）

Research on vertical structure LEDs

16:20-16:45 Hua Yang （Institute of Semiconductors, CAS）

Investigation of GaN-based LEDs using ZnO Transparent Electrode

16:45-17:10 Meng Liang （Institute of Semiconductors, CAS）

Thermal design of high-brightness LED module